

**Applications**

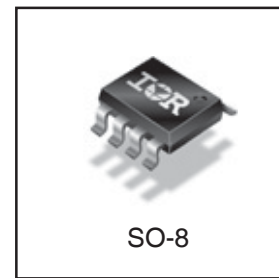
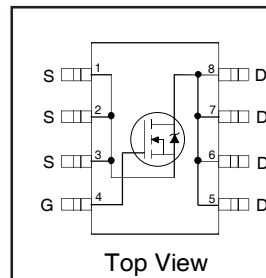
- High Frequency DC-DC Isolated Converters with Synchronous Rectification for Telecom and Industrial use
- High Frequency Buck Converters for Computer Processor Power
- Lead-Free

HEXFET® Power MOSFET

<b>V<sub>DSS</sub></b>	<b>R<sub>DS(on)</sub> max</b>	<b>I<sub>D</sub></b>
<b>30V</b>	<b>8mΩ</b>	<b>14A</b>

**Benefits**

- Ultra-Low Gate Impedance
- Very Low R<sub>DS(on)</sub> at 4.5V V<sub>GS</sub>
- Fully Characterized Avalanche Voltage and Current



**Absolute Maximum Ratings**

Symbol	Parameter	Max.	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GS</sub>	Gate-to-Source Voltage	± 12	V
I <sub>D</sub> @ T <sub>A</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	14	A
I <sub>D</sub> @ T <sub>A</sub> = 70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	11	
I <sub>DM</sub>	Pulsed Drain Current <sup>①</sup>	110	
P <sub>D</sub> @ T <sub>A</sub> = 25°C	Maximum Power Dissipation	2.5	W
P <sub>D</sub> @ T <sub>A</sub> = 70°C	Maximum Power Dissipation	1.6	W
	Linear Derating Factor	0.02	mW/°C
T <sub>J</sub> , T <sub>STG</sub>	Junction and Storage Temperature Range	-55 to + 150	°C

**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
R <sub>θJL</sub>	Junction-to-Drain Lead <sup>⑤</sup>	—	20	°C/W
R <sub>θJA</sub>	Junction-to-Ambient <sup>④⑤</sup>	—	50	

Notes <sup>①</sup> through <sup>⑤</sup> are on page 8  
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# IRF7463PbF

Static @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

International  
IR Rectifier

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.029	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	6.0	8.0	m $\Omega$	$V_{GS} = 10V, I_D = 14A$ ③
		—	7.0	9.5		$V_{GS} = 4.5V, I_D = 11A$ ③
		—	10.5	20		$V_{GS} = 2.7V, I_D = 7.0A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	0.6	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	20	$\mu A$	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	100		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 12V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -12V$

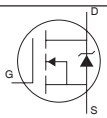
## Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$g_{fs}$	Forward Transconductance	41	—	—	S	$V_{DS} = 24V, I_D = 11A$
$Q_g$	Total Gate Charge	—	34	51	nC	$I_D = 11A$
$Q_{gs}$	Gate-to-Source Charge	—	7.6	11.4		$V_{DS} = 15V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	12	18		$V_{GS} = 4.5V$ ③
$Q_{oss}$	Output Gate Charge	—	21	32		$V_{GS} = 0V, V_{DS} = 15V$
$t_{d(on)}$	Turn-On Delay Time	—	16	—	ns	$V_{DD} = 15V$
$t_r$	Rise Time	—	138	—		$I_D = 11A$
$t_{d(off)}$	Turn-Off Delay Time	—	28	—		$R_G = 1.8\Omega$
$t_f$	Fall Time	—	6.5	—		$V_{GS} = 4.5V$ ③
$C_{iss}$	Input Capacitance	—	3150	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	1070	—		$V_{DS} = 15V$
$C_{rss}$	Reverse Transfer Capacitance	—	180	—		$f = 1.0MHz$

## Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
$E_{AS}$	Single Pulse Avalanche Energy②	—	320	mJ
$I_{AR}$	Avalanche Current①	—	14	A

## Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	2.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	110		
$V_{SD}$	Diode Forward Voltage	—	0.52	1.3	V	$T_J = 25^\circ\text{C}, I_S = 11A, V_{GS} = 0V$ ③
		—	0.44	—		$T_J = 125^\circ\text{C}, I_S = 11A, V_{GS} = 0V$ ③
$t_{rr}$	Reverse Recovery Time	—	45	70	ns	$T_J = 25^\circ\text{C}, I_F = 11A, V_R = 15V$
$Q_{rr}$	Reverse Recovery Charge	—	65	100	nC	$di/dt = 100A/\mu s$ ③
$t_{rr}$	Reverse Recovery Time	—	50	75	ns	$T_J = 125^\circ\text{C}, I_F = 11A, V_R = 15V$
$Q_{rr}$	Reverse Recovery Charge	—	80	120	nC	$di/dt = 100A/\mu s$ ③

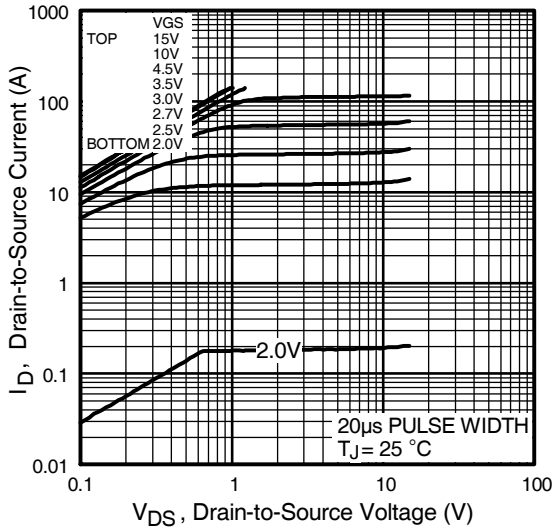


Fig 1. Typical Output Characteristics

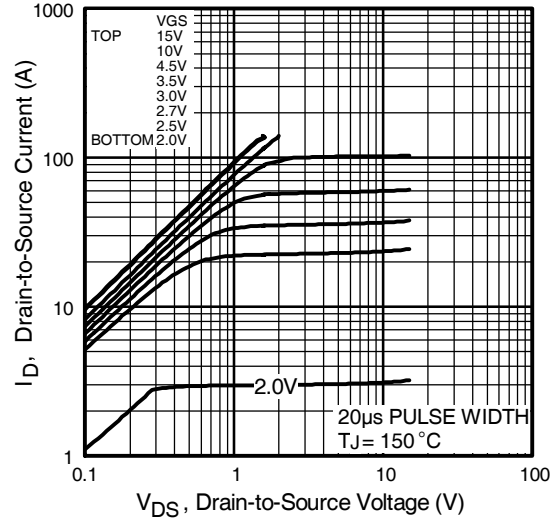


Fig 2. Typical Output Characteristics

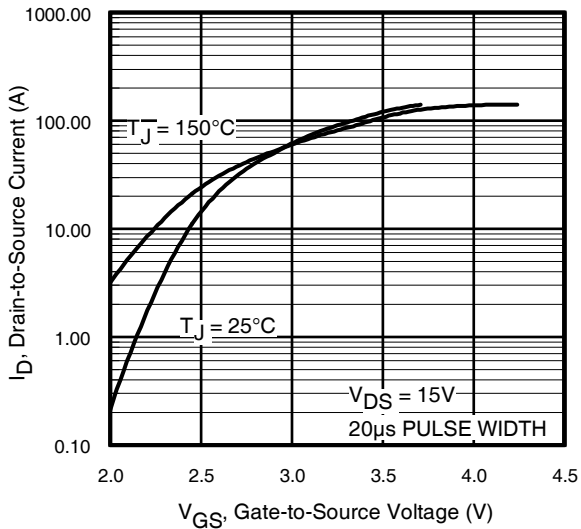


Fig 3. Typical Transfer Characteristics

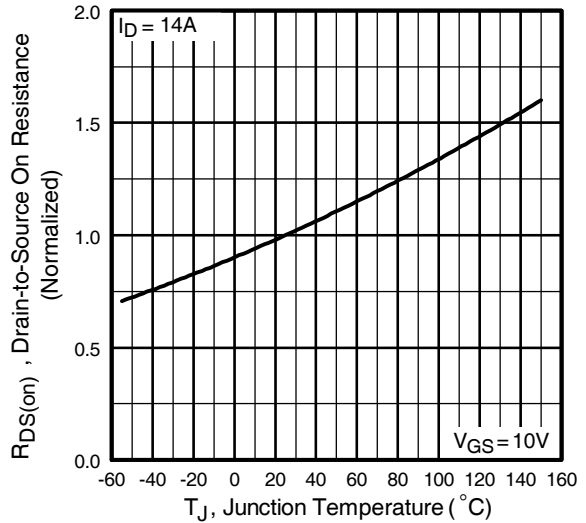
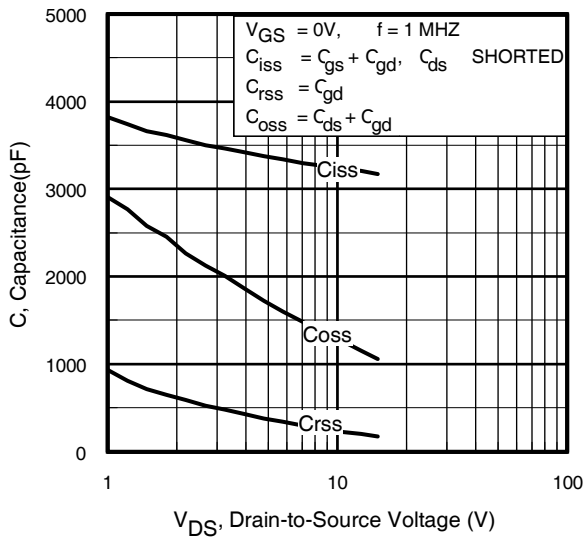
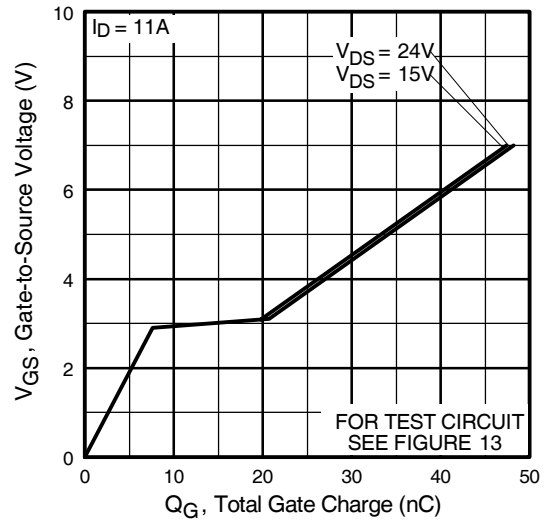


Fig 4. Normalized On-Resistance Vs. Temperature

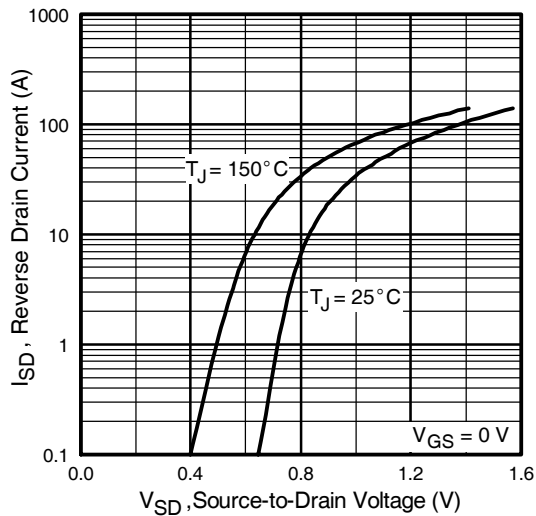
# IRF7463PbF



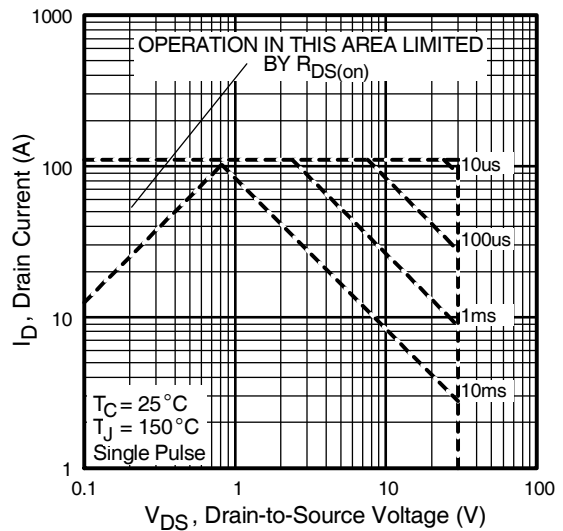
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



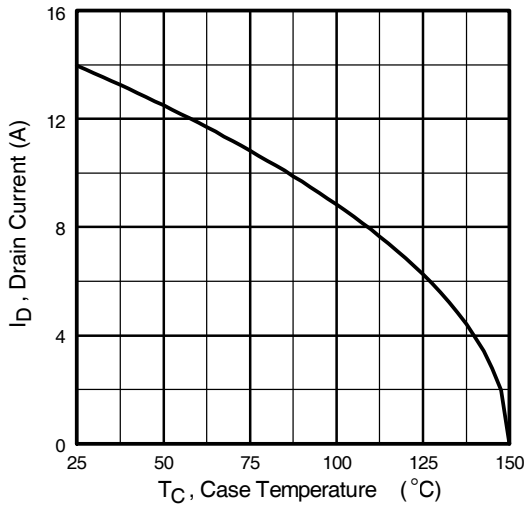
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



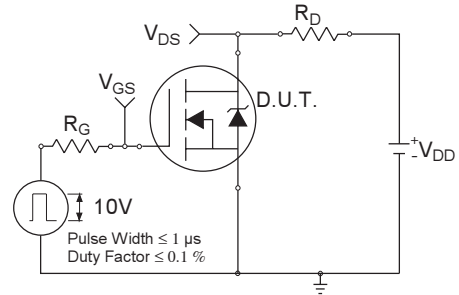
**Fig 7.** Typical Source-Drain Diode Forward Voltage



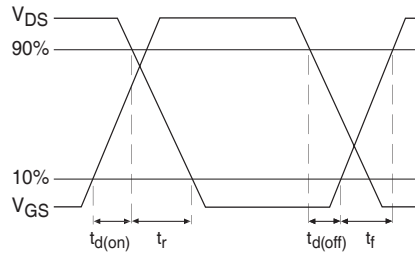
**Fig 8.** Maximum Safe Operating Area



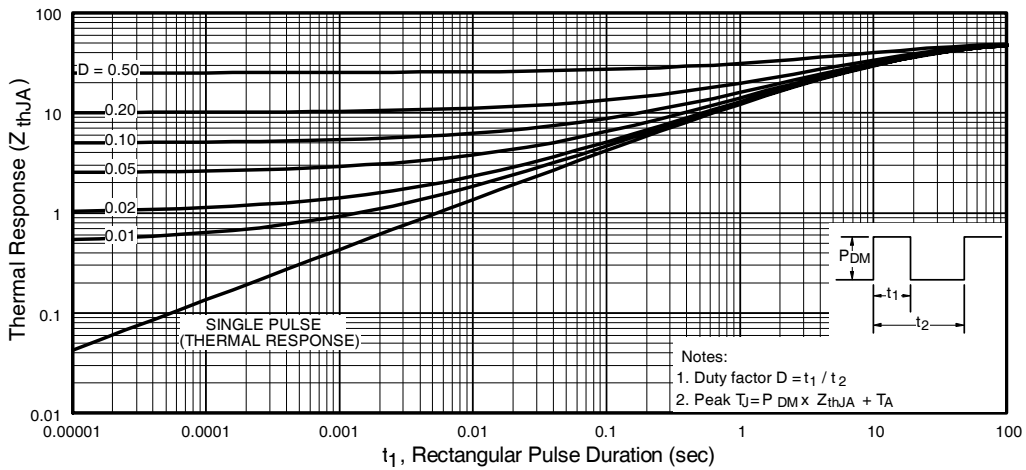
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



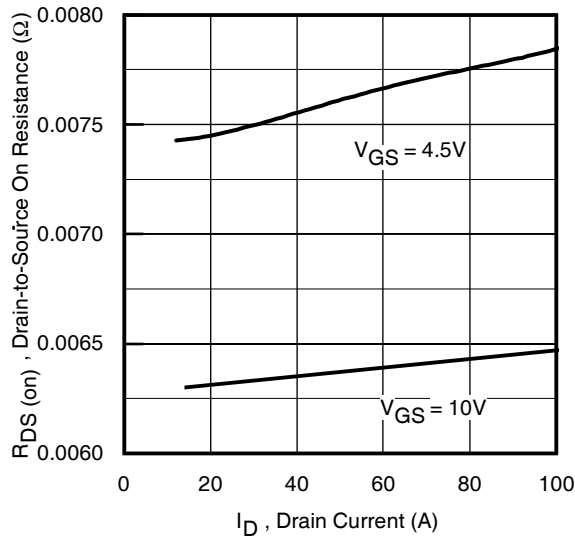
**Fig 10b.** Switching Time Waveforms



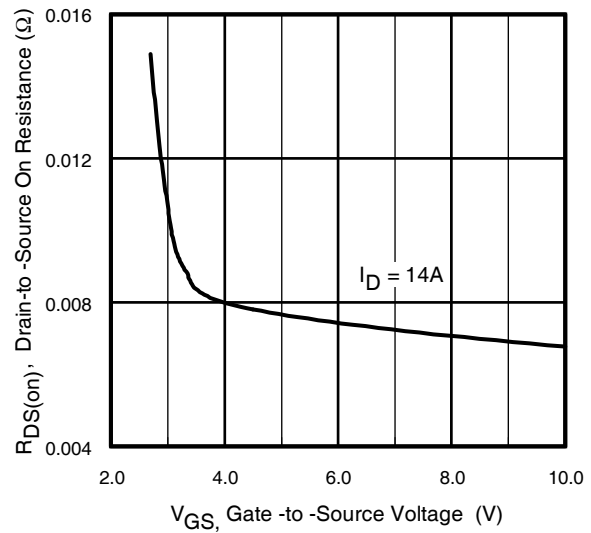
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

# IRF7463PbF

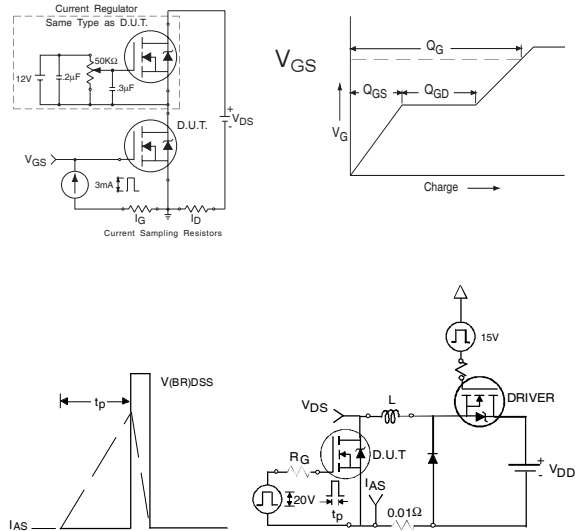
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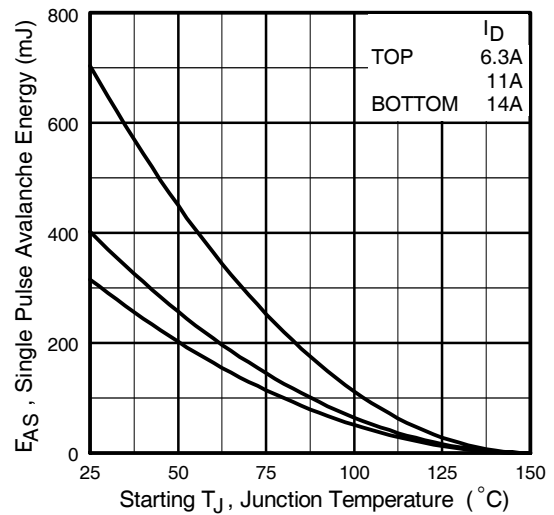
**Fig 12.** On-Resistance Vs. Drain Current



**Fig 13.** On-Resistance Vs. Gate Voltage



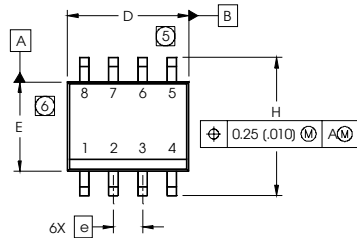
**Fig 15a&b.** Unclamped Inductive Test circuit and Waveforms



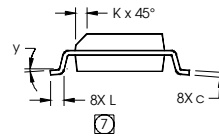
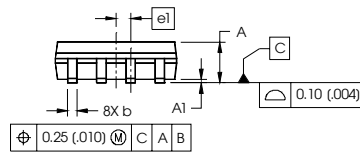
**Fig 15c.** Maximum Avalanche Energy Vs. Drain Current

## SO-8 Package Outline

Dimensions are shown in millimeters (inches)



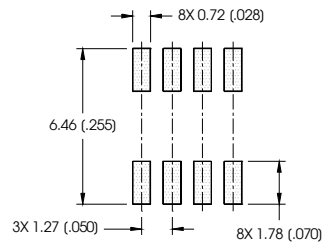
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



**NOTES:**

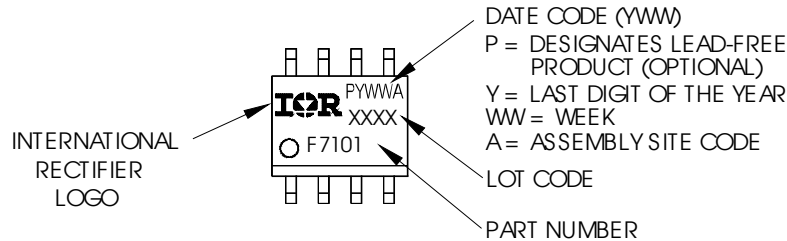
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

**FOOTPRINT**

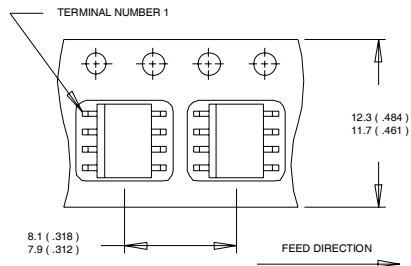


## SO-8 Part Marking Information (Lead-Free)

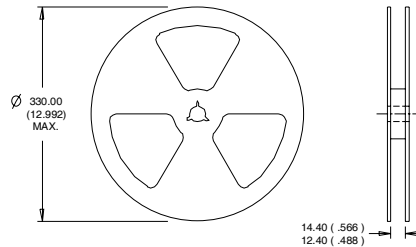
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



## SO-8 Tape and Reel



- NOTES:  
 1. CONTROLLING DIMENSION : MILLIMETER.  
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).  
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :  
 1. CONTROLLING DIMENSION : MILLIMETER.  
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 3.3\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 14\text{A}$ .
- ③ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ When mounted on 1 inch square copper board,  $t < 10\text{ sec}$
- ⑤  $R_\theta$  is measured at  $T_J$  approximately  $90^\circ\text{C}$

Data and specifications subject to change without notice.  
 This product has been designed and qualified for the Consumer market.  
 Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

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